NSL **Naina Semiconductor Ltd.**

130NDD

Diode – Diode Module

Features

- Improved glass passivation for high reliability
- Exceptional stability at high temperatures
- High di/dt and dv/dt capabilities
- Low thermal resistance

Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Values	Units
Maximum average forward current @ T_J = 85°C	$I_{F(AV)}$	130	A
Maximum average RMS forward current	$I_{F(RMS)}$	204	A
Maximum non-repetitive surge current @ t = 10ms	I_{FSM}	3600	A
Maximum I^2t for fusing @ t = 10ms	I^2t	53	kA^2s

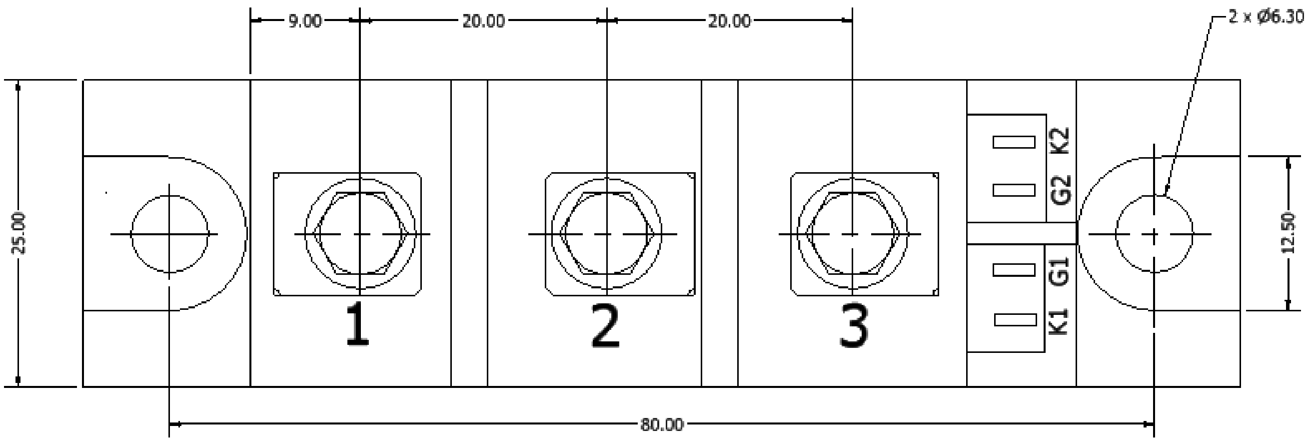
M2 PACKAGE

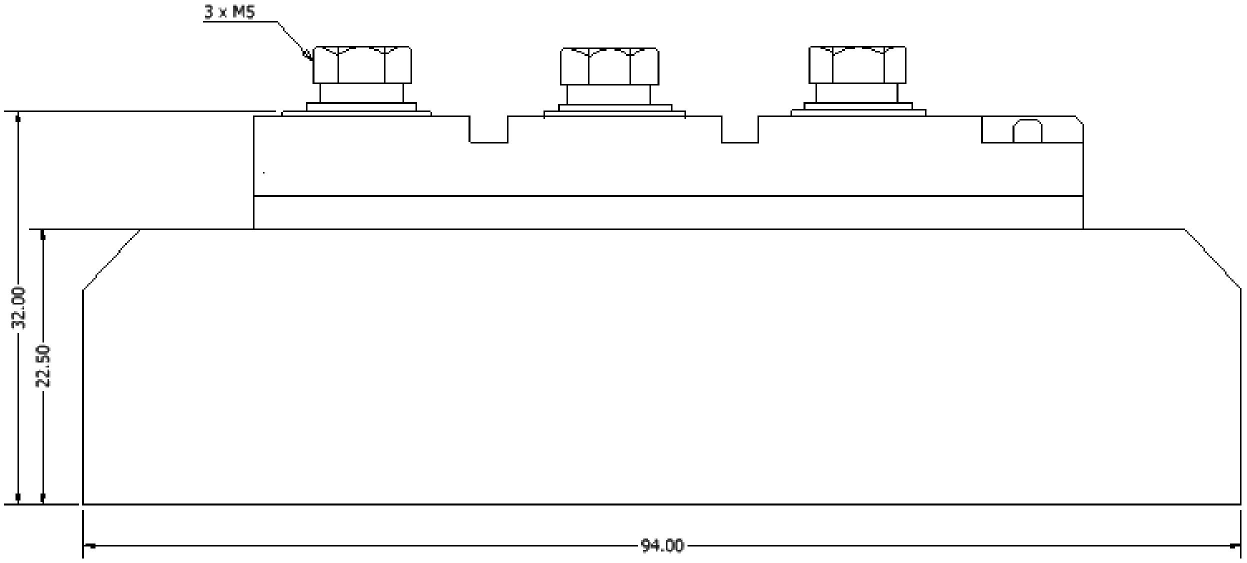
Thermal & Mechanical Specifications (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Values	Units
Operating junction temperature range	T_J	-65 to +125	°C
Thermal resistance, junction to case	$R_{th(JC)}$	0.2	°C/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Values	Units
Maximum average on-state current, 180°C sinusoidal	$I_{T(max)}$	130	A
Maximum repetitive peak reverse voltage range	V_{RRM}	200 to 1600	V
Forward voltage drop	V_{FM}	1.35	V
RMS isolation voltage	V_{ISO}	2500	V





ALL DIMENSIONS ARE IN MM

Diode Configuration